

ABSTRACT

The present invention provides an etching composition which includes a polyhydric alcohol in combination with two inorganic acids. Preferably the etching composition of the present invention is a mixture of a glycol, nitric acid and hydrofluoric acid, with propylene glycol being preferred. The etching composition of the present invention achieves a selectivity of greater than 70:1, doped material to undoped material. The present invention provides an etching formulation which has increased selectivity of doped polysilicon to undoped polysilicon and provides an efficient integrated circuit fabrication process without requiring time consuming and costly processing modifications to the etching apparatus or production apparatus.

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